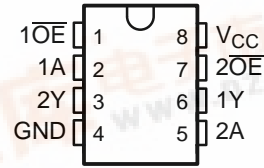


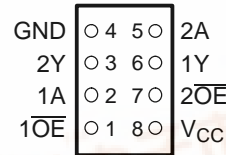
FEATURES

- Available in the Texas Instruments NanoStar™ and NanoFree™ Packages
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max t_{pd} of 4.3 ns at 3.3 V
- Low Power Consumption, 10- μ A Max I_{CC}
- ± 24 -mA Output Drive at 3.3 V
- Typical V_{OLP} (Output Ground Bounce) < 0.8 V at $V_{CC} = 3.3$ V, $T_A = 25^\circ\text{C}$
- Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at $V_{CC} = 3.3$ V, $T_A = 25^\circ\text{C}$
- I_{off} Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

DCT OR DCU PACKAGE
(TOP VIEW)



YEA, YEP, YZA, OR YZP PACKAGE
(BOTTOM VIEW)



DESCRIPTION/ORDERING INFORMATION

The SN74LVC2G125 is a dual bus buffer gate, designed for 1.65-V to 5.5-V V_{CC} operation. This device features dual line drivers with 3-state outputs. The outputs are disabled when the associated output-enable (\overline{OE}) input is high.

NanoStar™ and NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

ORDERING INFORMATION

T_A	PACKAGE ⁽¹⁾		ORDERABLE PART NUMBER	TOP-SIDE MARKING ⁽²⁾
-40°C to 85°C	NanoStar™ – WCSP (DSBGA) 0.17-mm Small Bump – YEA	Reel of 3000	SN74LVC2G125YEAR	---CM_
	NanoFree™ – WCSP (DSBGA) 0.17-mm Small Bump – YZA (Pb-free)		SN74LVC2G125YZAR	
	NanoStar™ – WCSP (DSBGA) 0.23-mm Large Bump – YEP		SN74LVC2G125YEPR	
	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)		SN74LVC2G125YZPR	
	SSOP – DCT	Reel of 3000	SN74LVC2G125DCTR	C25_ _ _
	VSSOP – DCU	Reel of 3000	SN74LVC2G125DCUR	C25_
Reel of 250			SN74LVC2G125DCUT	

(1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

(2) DCT: The actual top-side marking has three additional characters that designate the year, month, and assembly/test site.
DCU: The actual top-side marking has one additional character that designates the assembly/test site.

YEA/YZA, YEP/YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, • = Pb-free).

SN74LVC2G125 DUAL BUS BUFFER GATE WITH 3-STATE OUTPUTS

SCES204K—APRIL 1999—REVISED JUNE 2005



DESCRIPTION/ORDERING INFORMATION (CONTINUED)

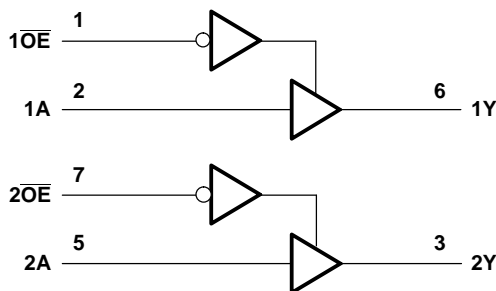
To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

**FUNCTION TABLE
(EACH BUFFER)**

INPUTS		OUTPUT Y
\overline{OE}	A	
L	H	H
L	L	L
H	X	Z

LOGIC DIAGRAM (POSITIVE LOGIC)



Absolute Maximum Ratings⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V_{CC}	Supply voltage range	-0.5	6.5	V
V_I	Input voltage range ⁽²⁾	-0.5	6.5	V
V_O	Voltage range applied to any output in the high-impedance or power-off state ⁽²⁾	-0.5	6.5	V
V_O	Voltage range applied to any output in the high or low state ⁽²⁾⁽³⁾	-0.5	$V_{CC} + 0.5$	V
I_{IK}	Input clamp current	$V_I < 0$	-50	mA
I_{OK}	Output clamp current	$V_O < 0$	-50	mA
I_O	Continuous output current		±50	mA
	Continuous current through V_{CC} or GND		±100	mA
θ_{JA}	Package thermal impedance ⁽⁴⁾	DCT package		°C/W
		DCU package		
		YEA/YZA package		
		YEP/YZP package		
T_{stg}	Storage temperature range	-65	150	°C

- Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- The value of V_{CC} is provided in the recommended operating conditions table.
- The package thermal impedance is calculated in accordance with JESD 51-7.

Recommended Operating Conditions⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage	Operating	1.65	5.5	V
		Data retention only	1.5		
V _{IH}	High-level input voltage	V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}		V
		V _{CC} = 2.3 V to 2.7 V	1.7		
		V _{CC} = 3 V to 3.6 V	2		
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}		
V _{IL}	Low-level input voltage	V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V		0.7	
		V _{CC} = 3 V to 3.6 V		0.8	
		V _{CC} = 4.5 V to 5.5 V		0.3 × V _{CC}	
V _I	Input voltage		0	5.5	V
V _O	Output voltage	High or low state	0	V _{CC}	V
		3-state	0	5.5	
I _{OH}	High-level output current	V _{CC} = 1.65 V		–4	mA
		V _{CC} = 2.3 V		–8	
		V _{CC} = 3 V		–16	
		V _{CC} = 4.5 V		–24	
I _{OL}	Low-level output current	V _{CC} = 1.65 V		4	mA
		V _{CC} = 2.3 V		8	
		V _{CC} = 3 V		16	
		V _{CC} = 4.5 V		24	
Δt/Δv	Input transition rise or fall rate	V _{CC} = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20	ns/V
		V _{CC} = 3.3 V ± 0.3 V		10	
		V _{CC} = 5 V ± 0.5 V		5	
T _A	Operating free-air temperature		–40	85	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

SN74LVC2G125 DUAL BUS BUFFER GATE WITH 3-STATE OUTPUTS



SCES204K–APRIL 1999–REVISED JUNE 2005

Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V _{CC}	MIN	TYP ⁽¹⁾	MAX	UNIT
V _{OH}		I _{OH} = -100 μA	1.65 V to 5.5 V	V _{CC} - 0.1			V
		I _{OH} = -4 mA	1.65 V	1.2			
		I _{OH} = -8 mA	2.3 V	1.9			
		I _{OH} = -16 mA	3 V	2.4			
		I _{OH} = -24 mA		2.3			
		I _{OH} = -32 mA	4.5 V	3.8			
V _{OL}		I _{OL} = 100 μA	1.65 V to 5.5 V			0.1	V
		I _{OL} = 4 mA	1.65 V			0.45	
		I _{OL} = 8 mA	2.3 V			0.3	
		I _{OL} = 16 mA	3 V			0.4	
		I _{OL} = 24 mA				0.55	
		I _{OL} = 32 mA	4.5 V			0.55	
I _I	A or \overline{OE} inputs	V _I = 5.5 V or GND	0 to 5.5 V			±5	μA
I _{off}		V _I or V _O = 5.5 V	0			±10	μA
I _{OZ}		V _O = 0 to 5.5 V	3.6 V			10	μA
I _{CC}		V _I = 5.5 V or GND, I _O = 0	1.65 V to 5.5 V			10	μA
ΔI _{CC}		One input at V _{CC} - 0.6 V, Other inputs at V _{CC} or GND	3 V to 5.5 V			500	μA
C _i	Data inputs	V _I = V _{CC} or GND	3.3 V			3.5	pF
	Control inputs					4	
C _o		V _O = V _{CC} or GND	3.3 V			6.5	pF

(1) All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

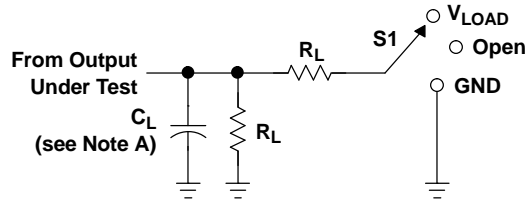
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A	Y	3.3	9.1	1.5	4.8	1.4	4.3	1	3.7	ns
t _{en}	\overline{OE}	Y	4	9.9	1.9	5.6	1.2	4.7	1.2	3.8	ns
t _{dis}	\overline{OE}	Y	1.5	11.6	1	5.8	1.4	4.6	1	3.4	ns

Operating Characteristics

T_A = 25°

PARAMETER		TEST CONDITIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	V _{CC} = 5 V	UNIT
			TYP	TYP	TYP	TYP	
C _{pd}	Power dissipation capacitance	Outputs enabled	19	19	20	22	pF
		Outputs disabled	2	2	2	3	

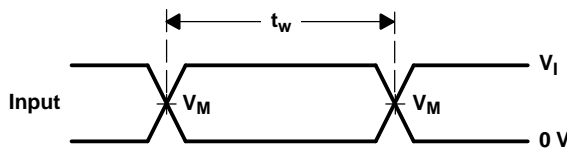
PARAMETER MEASUREMENT INFORMATION



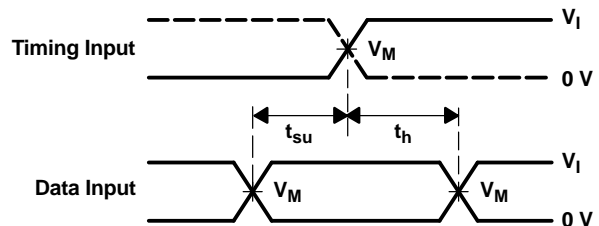
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

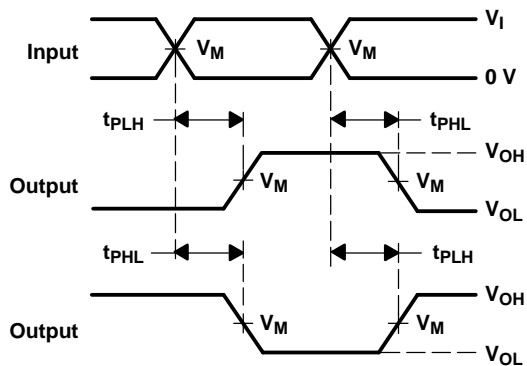
V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_{Δ}
	V_I	t_r/t_f					
$1.8\text{ V} \pm 0.15\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	1 k Ω	0.15 V
$2.5\text{ V} \pm 0.2\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	500 Ω	0.15 V
$3.3\text{ V} \pm 0.3\text{ V}$	3 V	$\leq 2.5\text{ ns}$	1.5 V	6 V	50 pF	500 Ω	0.3 V
$5\text{ V} \pm 0.5\text{ V}$	V_{CC}	$\leq 2.5\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	50 pF	500 Ω	0.3 V



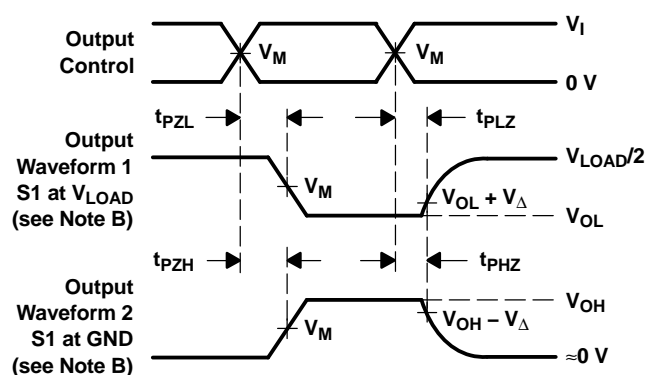
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

- NOTES: A. C_L includes probe and jig capacitance.
 B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_O = 50\ \Omega$.
 D. The outputs are measured one at a time, with one transition per measurement.
 E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 F. t_{PZL} and t_{PZH} are the same as t_{en} .
 G. t_{PLH} and t_{PHL} are the same as t_{pd} .
 H. All parameters and waveforms are not applicable to all devices.

Figure 1. Load Circuit and Voltage Waveforms

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
74LVC2G125DCTRE4	ACTIVE	SM8	DCT	8	3000	Pb-Free (RoHS)	CU NIPDAU	Level-1-260C-UNLIM
74LVC2G125DCTRE6	ACTIVE	SM8	DCT	8	3000	Pb-Free (RoHS)	CU SNBI	Level-1-260C-UNLIM
74LVC2G125DCURE4	ACTIVE	US8	DCU	8	3000	Pb-Free (RoHS)	CU NIPDAU	Level-1-260C-UNLIM
74LVC2G125DCUTE4	ACTIVE	US8	DCU	8	250	Pb-Free (RoHS)	CU NIPDAU	Level-1-260C-UNLIM
SN74LVC2G125DCTR	ACTIVE	SM8	DCT	8	3000	Pb-Free (RoHS)	CU NIPDAU	Level-1-260C-UNLIM
SN74LVC2G125DCUR	ACTIVE	US8	DCU	8	3000	Pb-Free (RoHS)	CU NIPDAU	Level-1-260C-UNLIM
SN74LVC2G125DCUT	ACTIVE	US8	DCU	8	250	Pb-Free (RoHS)	CU NIPDAU	Level-1-260C-UNLIM
SN74LVC2G125YEAR	ACTIVE	WCSP	YEA	8	3000	TBD	SNPB	Level-1-260C-UNLIM
SN74LVC2G125YEPR	ACTIVE	WCSP	YEP	8	3000	TBD	SNPB	Level-1-260C-UNLIM
SN74LVC2G125YZAR	ACTIVE	WCSP	YZA	8	3000	Pb-Free (RoHS)	SNAGCU	Level-1-260C-UNLIM
SN74LVC2G125YZPR	ACTIVE	WCSP	YZP	8	3000	Pb-Free (RoHS)	SNAGCU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS) or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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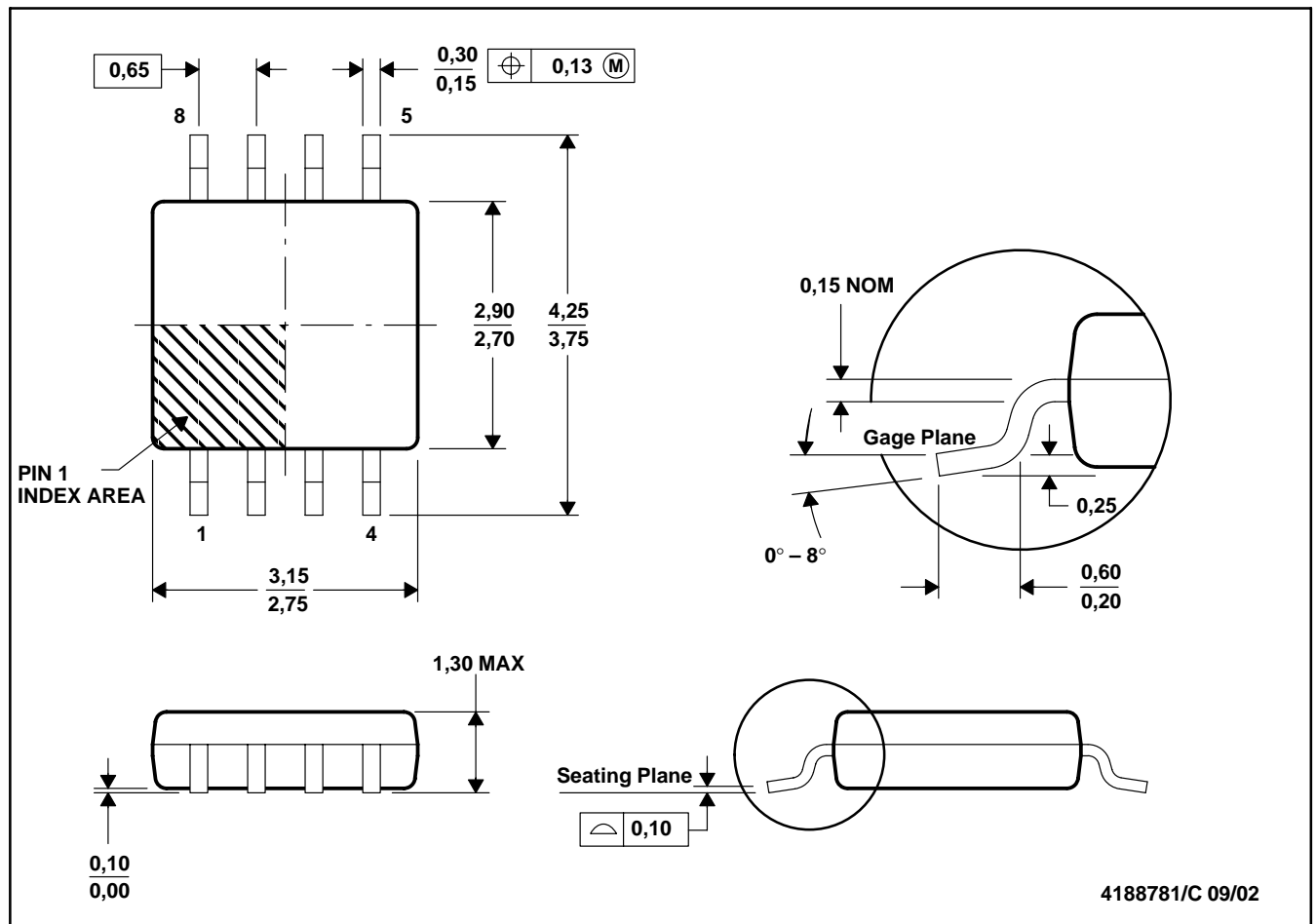
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MECHANICAL DATA

MPDS049B – MAY 1999 – REVISED OCTOBER 2002

DCT (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE

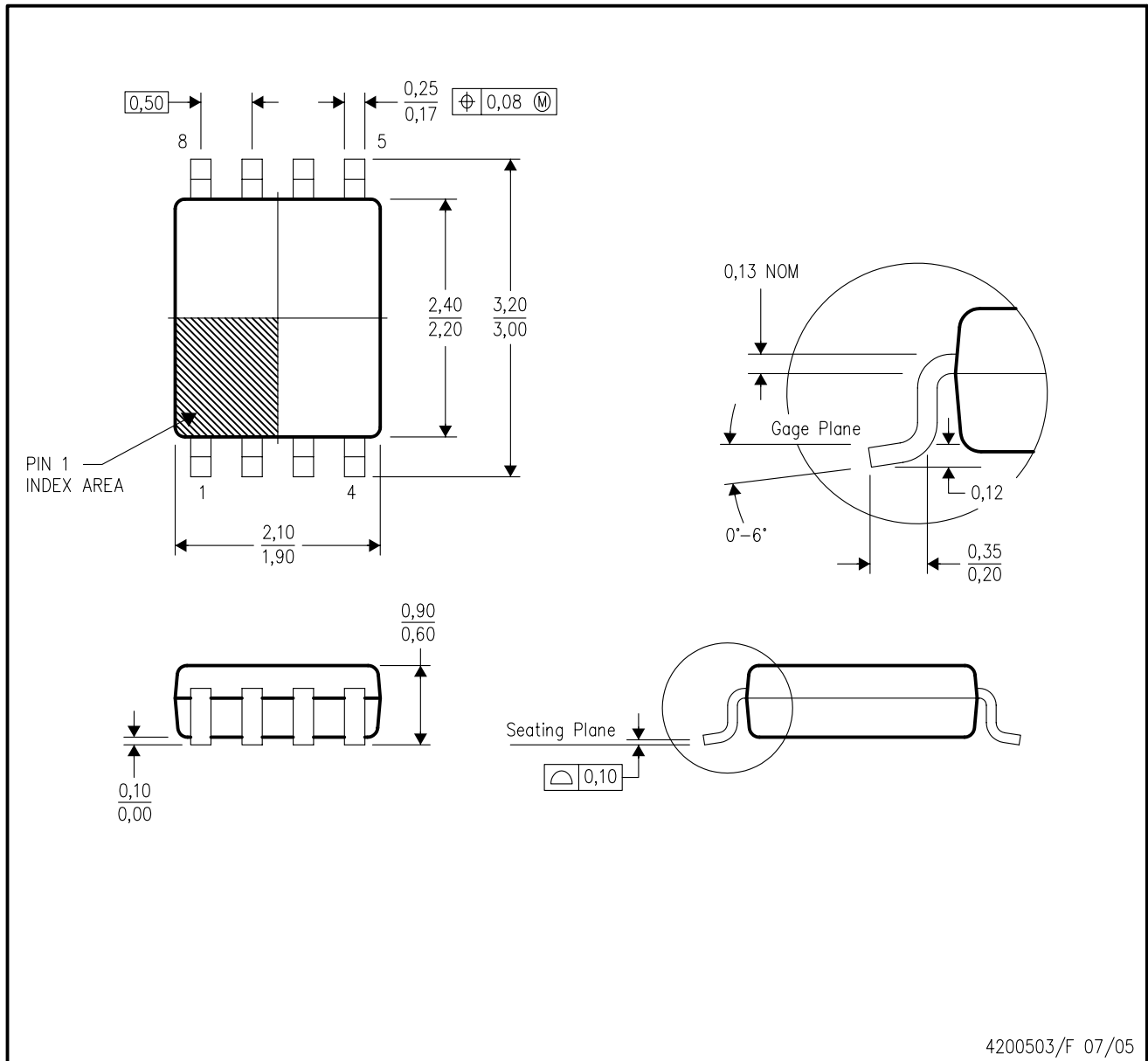


- NOTES: A. All linear dimensions are in millimeters.
 B. This drawing is subject to change without notice.
 C. Body dimensions do not include mold flash or protrusion
 D. Falls within JEDEC MO-187 variation DA.

MECHANICAL DATA

DCU (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



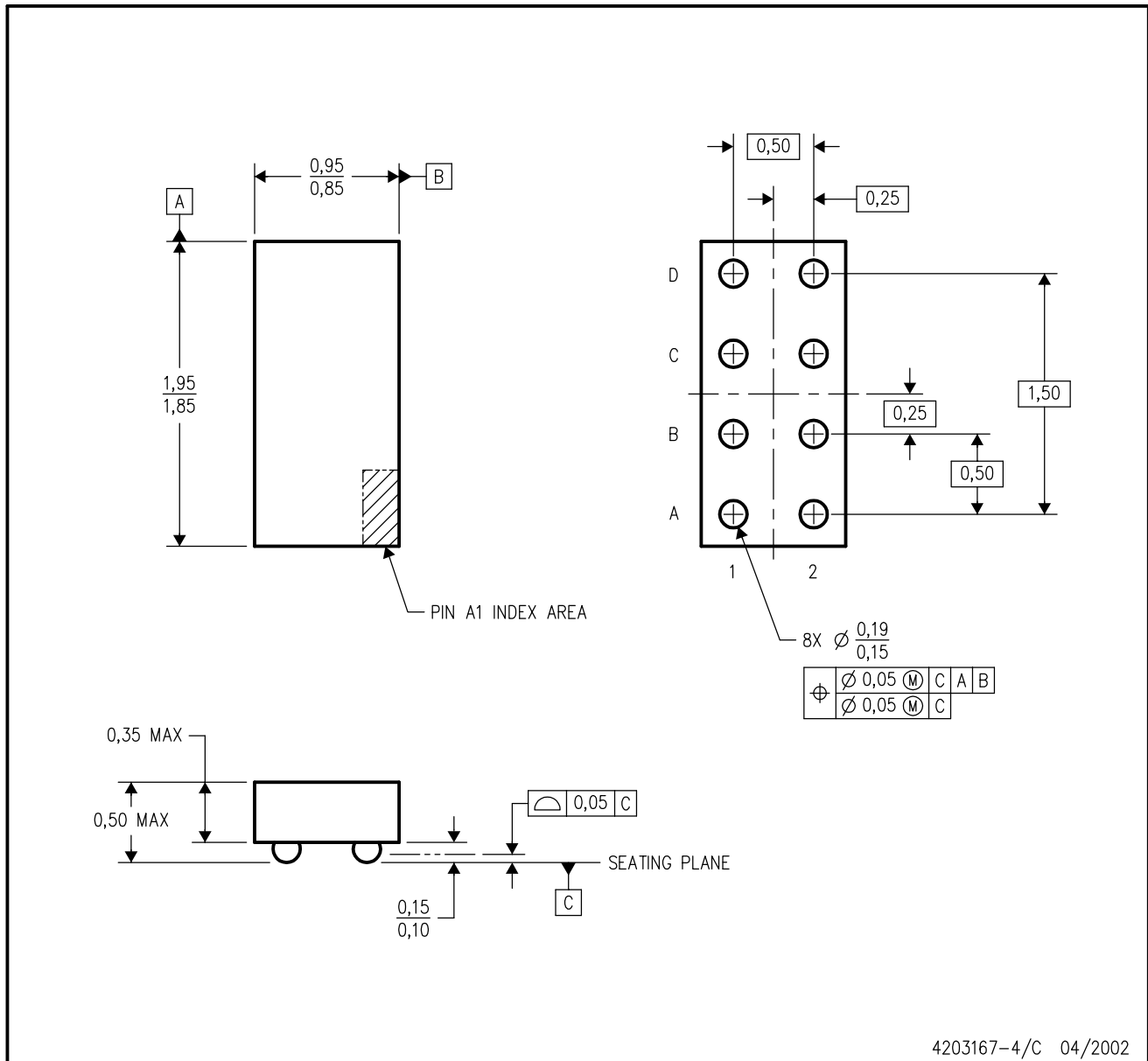
4200503/F 07/05

- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 - Falls within JEDEC MO-187 variation CA.

MECHANICAL DATA

YEA (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



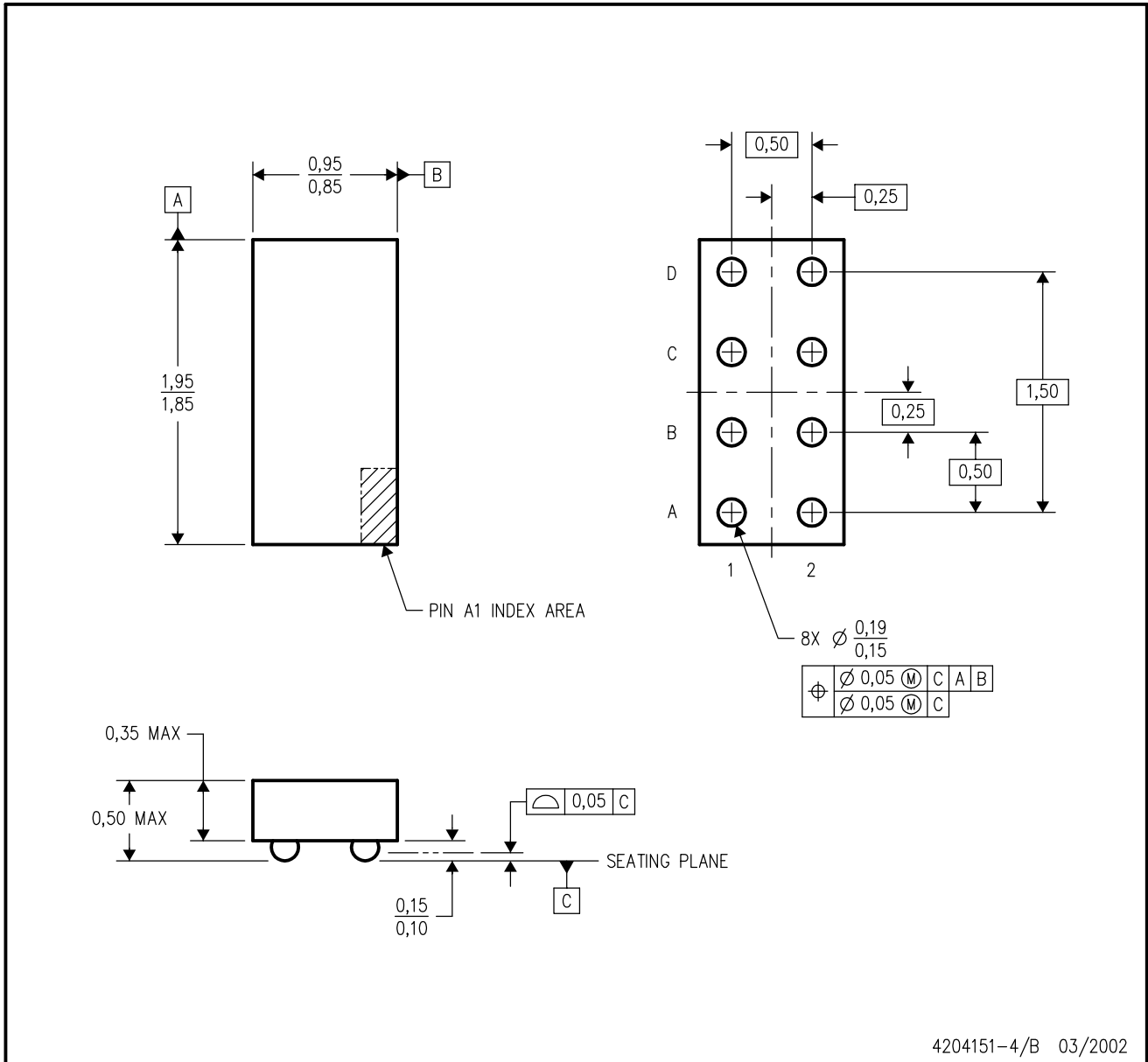
- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. NanoStar™ package configuration.
 - D. Package complies to JEDEC MO-211 variation EB.
 - E. This package is tin-lead (SnPb). Refer to the 8 YZA package (drawing 4204151) for lead-free.

NanoStar is a trademark of Texas Instruments.

MECHANICAL DATA

YZA (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



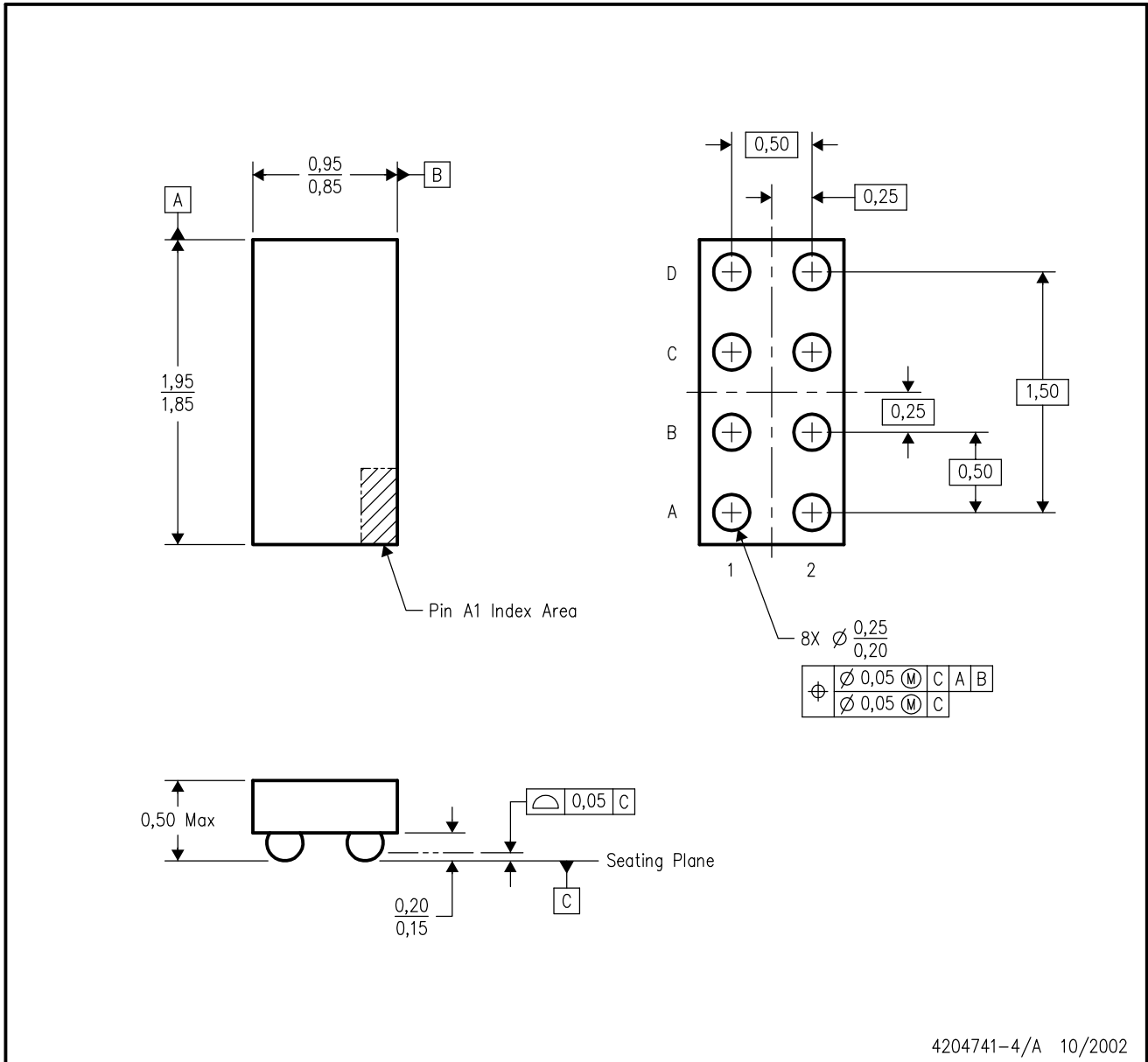
- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. NanoFree™ package configuration.
 - D. Package complies to JEDEC MO-211 variation EB.
 - E. This package is lead-free. Refer to the 8 YEA package (drawing 4203167) for tin-lead (SnPb).

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MECHANICAL DATA

YZP (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY

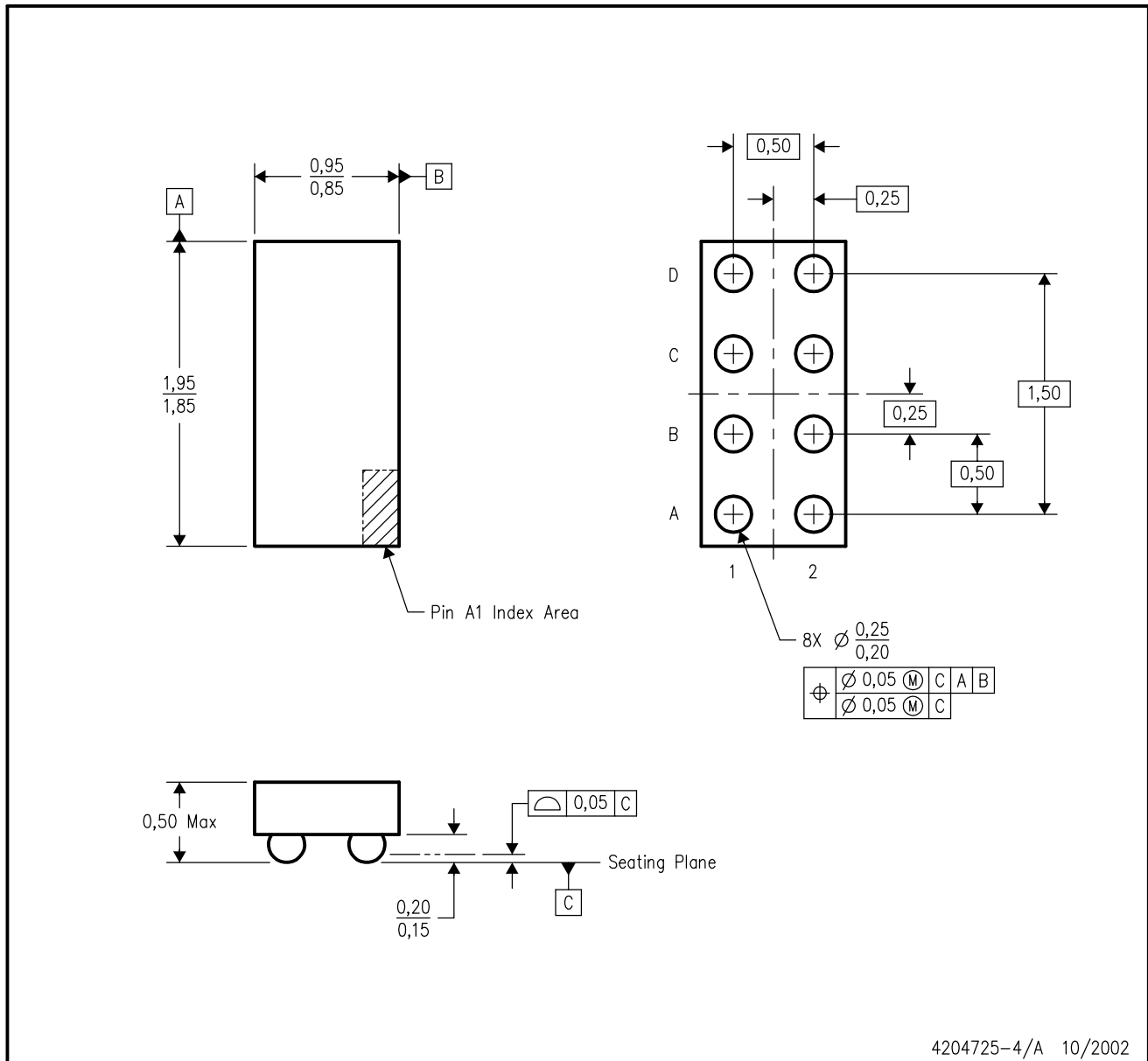


- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. NanoFree™ package configuration.
 - D. This package is lead-free. Refer to the 8 YEP package (drawing 4204725) for tin-lead (SnPb).

MECHANICAL DATA

YEP (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. NanoStar™ package configuration.
 - D. This package is tin-lead (SnPb). Refer to the 8 YZP package (drawing 4204741) for lead-free.

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